



3DD515

NPN Silicon Low Frequency High Power Transistor



Features:

1. Excellent second breakdown capacity. Good temperature stability.Excellent thermal fatigue capability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, low frequency power amplify, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

| Parameter name | Symbols | Unit | Specifications | Test Condition |
|--|---------------|------------------|------------------|---------------------------------------|
| Collector-Emitter Voltage | V_{CEO} | V | 200 | |
| Emitter-Base Voltage | V_{EBO} | V | 5 | |
| Max. Collector Current | I_{CM} | A | 15 | |
| Max. Collector Dissipation | P_{CM} | W | 150 | ($T_c=75^\circ\text{C}$) |
| Junction Temperature | T_{jm} | $^\circ\text{C}$ | 175 | |
| Storage Temperature | T_{stg} | $^\circ\text{C}$ | -65~+175 | |
| Collector-Emitter Leakage Current | I_{CBO} | mA | Max.:1.0 | $V_{CB}=250\text{V}$ |
| Collector- Emitter Saturation Voltage Drop | $V_{CE(sat)}$ | V | Max.:1.5 | $I_c=7.5\text{A}, I_B=1.5\text{A}$ |
| DC Current Gain | h_{FE} | | Max.:80, Min.:55 | $V_{CE}= 10\text{V}, I_c=7.5\text{A}$ |
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | V | 250 | $I_c=1\text{mA}$ |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | V | 200 | $I_c=2\text{mA}$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | V | 5 | $I_E=5\text{mA}$ |

Outline and Dimensions: